

## Features

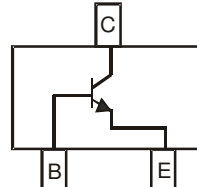
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complimentary PNP Type Available (DSS5320T)
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **“Green” Device (Note 2)**

## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

## Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	20	V
Collector-Emitter Voltage	$V_{CEO}$	20	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	5	A
Repetitive Peak Pulse Current (Note 3)	$I_{CRP}$	3	A
Continuous Collector Current	$I_C$	2	A
Base Current	$I_B$	0.5	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	$P_D$	600	mW
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	209	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Operated under pulse conditions: Pulse width  $\leq 100\text{ms}$ , duty cycle  $\leq 0.25$ .
  4. Device mounted on FR-4 PCB; with minimum recommended pad layout.

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
<b>OFF CHARACTERISTICS</b>						
Collector-Base Cutoff Current	$I_{CBO}$	—	—	100	nA	$V_{CB} = 20\text{V}, I_E = 0$
Emitter-Base Cutoff Current	$I_{EBO}$	—	—	50	$\mu\text{A}$	$V_{CB} = 20\text{V}, I_E = 0, T_A = 150^\circ\text{C}$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	20	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 100\mu\text{A}$
<b>ON CHARACTERISTICS (Note 5)</b>						
DC Current Gain	$h_{FE}$	220	—	—	—	$V_{CE} = 2\text{V}, I_C = 0.1\text{A}$
		220	—	—		$V_{CE} = 2\text{V}, I_C = 0.5\text{A}$
		220	—	—		$V_{CE} = 2\text{V}, I_C = 1\text{A}$
		200	—	—		$V_{CE} = 2\text{V}, I_C = 2\text{A}$
		150	—	—		$V_{CE} = 2\text{V}, I_C = 3\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	70	mV	$I_C = 0.5\text{A}, I_B = 50\text{mA}$
		—	—	120		$I_C = 1\text{A}, I_B = 50\text{mA}$
		—	—	230		$I_C = 2\text{A}, I_B = 40\text{mA}$
		—	70	210		$I_C = 2\text{A}, I_B = 200\text{mA}$
		—	—	310		$I_C = 3\text{A}, I_B = 300\text{mA}$
Equivalent On-Resistance	$R_{CE(SAT)}$	—	35	105	$\text{m}\Omega$	$I_E = 2\text{A}, I_B = 200\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	1.1	V	$I_C = 2\text{A}, I_B = 40\text{mA}$
		—	—	1.2	V	$I_C = 3\text{A}, I_B = 300\text{mA}$
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	1.2	V	$V_{CE} = 2\text{V}, I_C = 1\text{A}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	$f_T$	100	—	—	MHz	$V_{CE} = 5\text{V}, I_C = 100\text{mA}, f = 100\text{MHz}$
Output Capacitance	$C_{ob}$	—	—	35	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

Notes: 5. Measured under pulsed conditions. Pulse width = 300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

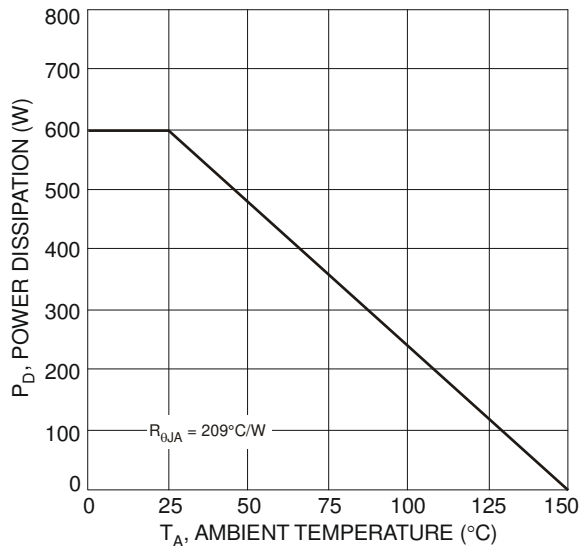


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 4)

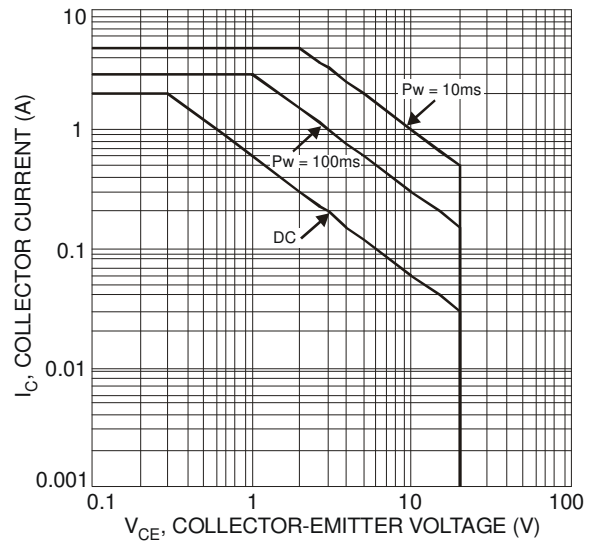


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

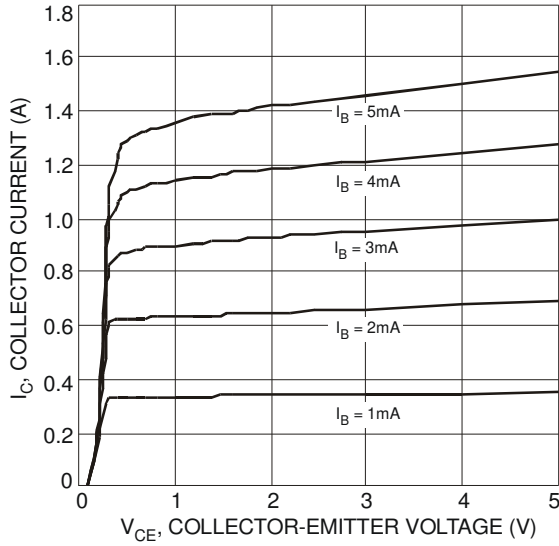


Fig. 3 Typical Collector Current vs. Collector-Emitter Voltage

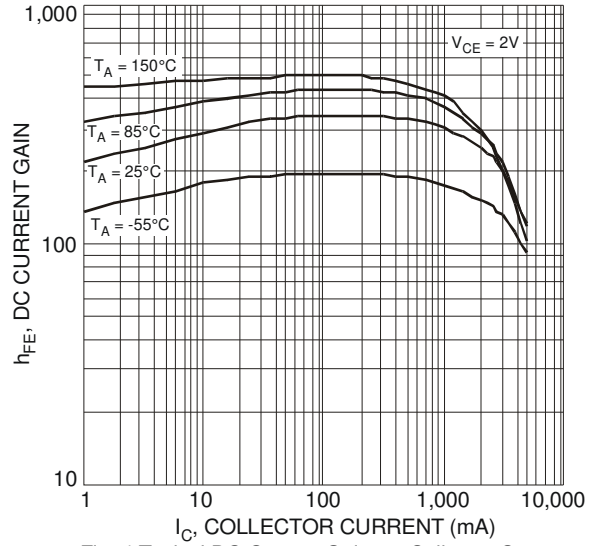


Fig. 4 Typical DC Current Gain vs. Collector Current

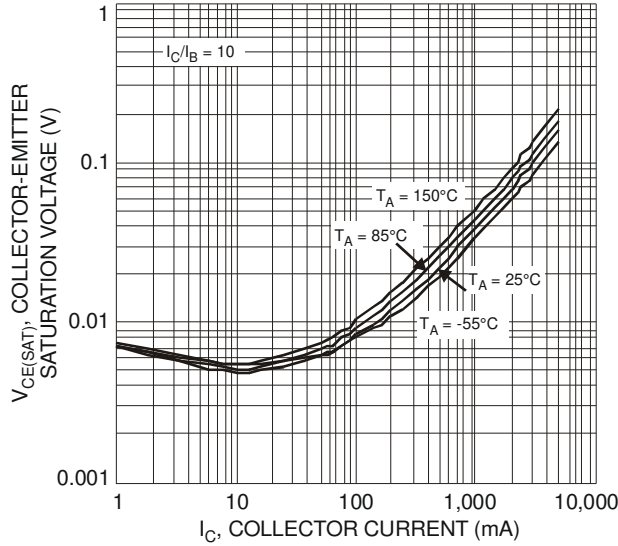


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

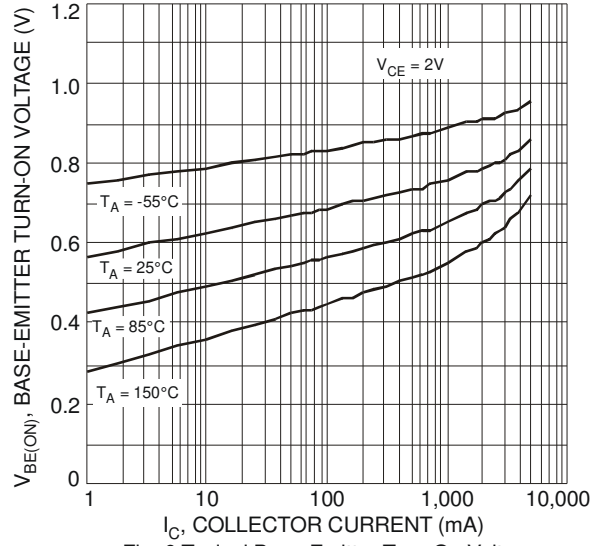


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

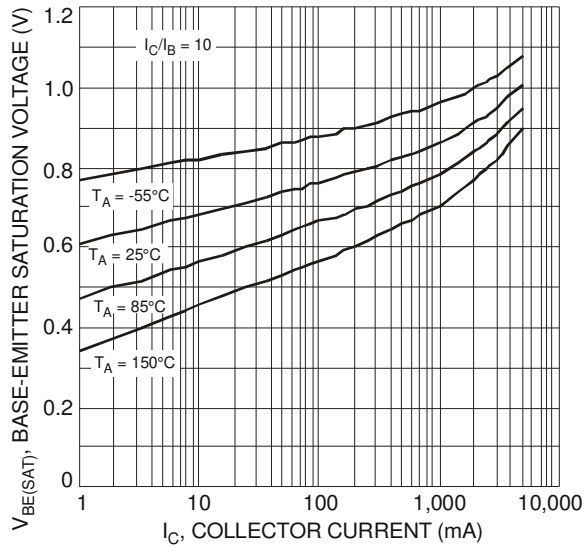


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

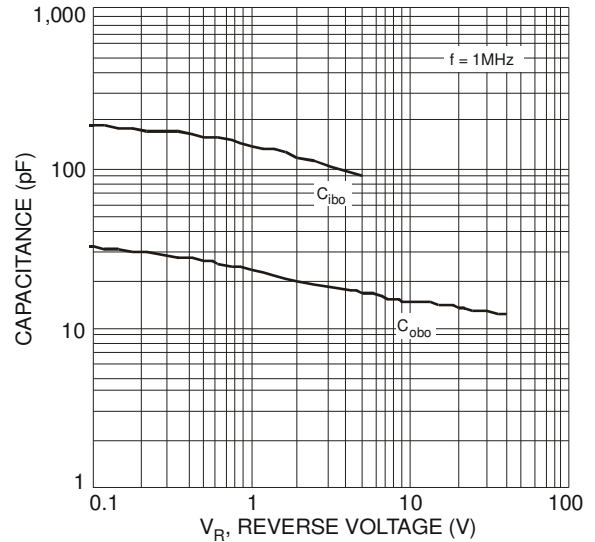


Fig. 8 Typical Capacitance Characteristics

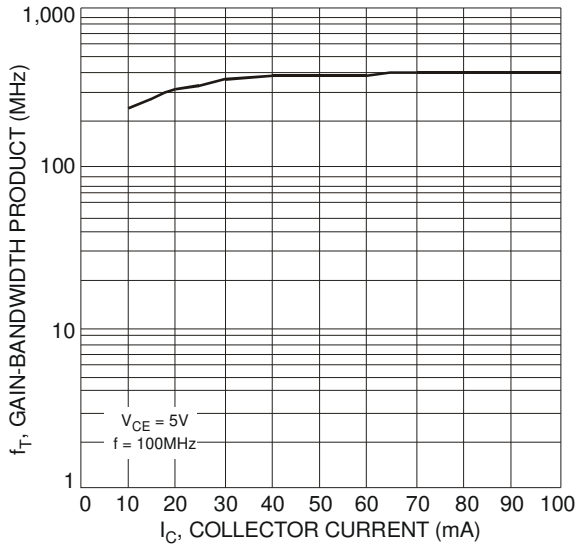


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

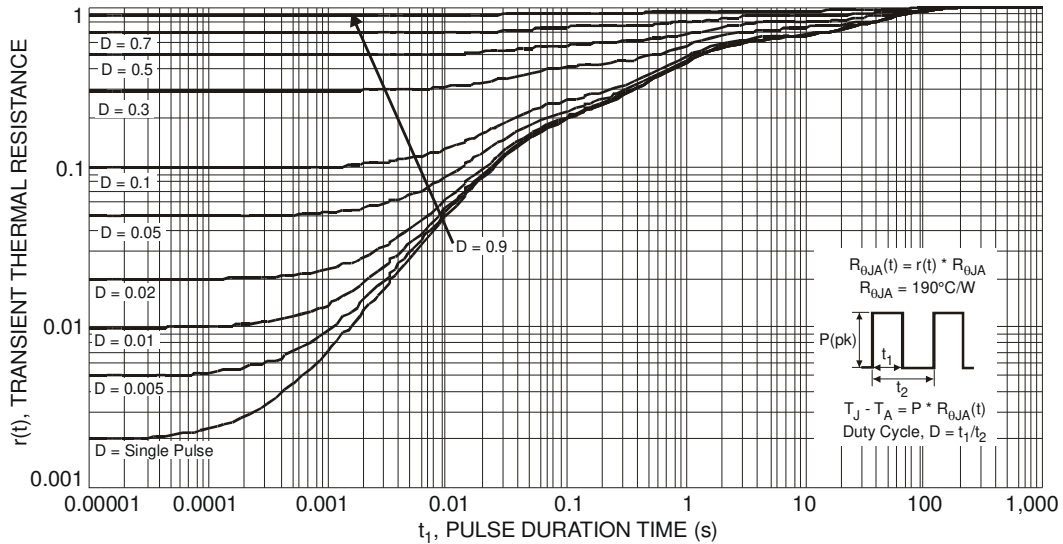


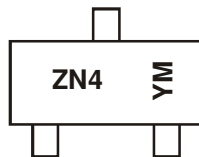
Fig. 10 Transient Thermal Response

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DSS4320T-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**

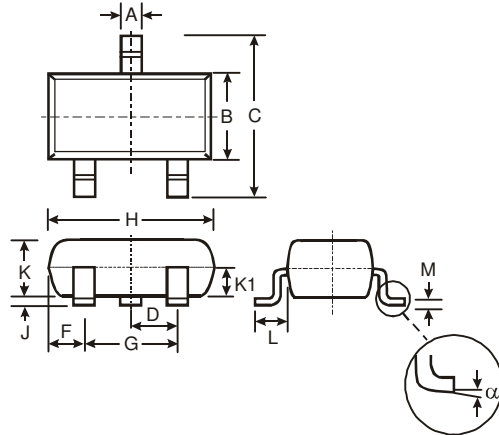


ZN4 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: V = 2008)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015				
Code	V	W	X	Y	Z	A	B	C				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

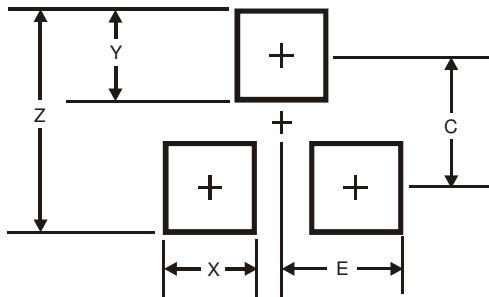
**Package Outline Dimensions**



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

**All Dimensions in mm**

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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